# onsemi

## Inverting Regulator - Buck, Boost, Switching

## 1.5 A

## MC34063A, MC33063A, SC33063A, NCV33063A

The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step–Down and Step–Up and Voltage–Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

#### Features

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

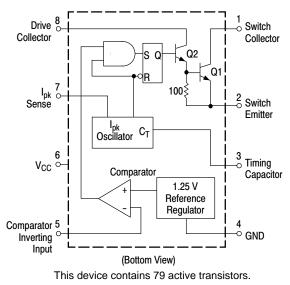
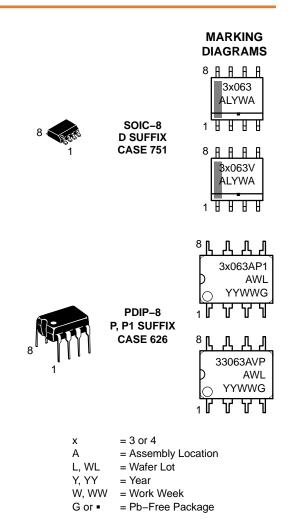


Figure 1. Representative Schematic Diagram



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

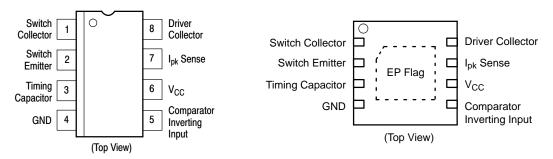


Figure 2. Pin Connections

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub>	40	Vdc
Comparator Input Voltage Range	V <sub>IR</sub>	-0.3 to +40	Vdc
Switch Collector Voltage	V <sub>C(switch)</sub>	40	Vdc
Switch Emitter Voltage (V <sub>Pin 1</sub> = 40 V)	V <sub>E(switch)</sub>	40	Vdc
Switch Collector to Emitter Voltage	V <sub>CE(switch)</sub>	40	Vdc
Driver Collector Voltage	V <sub>C(driver)</sub>	40	Vdc
Driver Collector Current (Note 1)	I <sub>C(driver)</sub>	100	mA
Switch Current	I <sub>SW</sub>	1.5	А
Power Dissipation and Thermal Characteristics			
Plastic Package, P, P1 Suffix			
$T_A = 25^{\circ}C$	PD	1.25	W
Thermal Resistance	R <sub>θJA</sub>	115	°C/W
SOIC Package, D Suffix			
$T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance	R <sub>θJA</sub>	160	°C/W
Thermal Resistance	$R_{\theta JC}$	45	°C/W
DFN Package			
$T_A = 25^{\circ}C$	PD	1.25	mW
Thermal Resistance	$R_{ ext{ heta}JA}$	80	°C/W
Operating Junction Temperature	ТJ	+150	°C
Operating Ambient Temperature Range	T <sub>A</sub>		°C
MC34063A		0 to +70	
MC33063AV, NCV33063A		-40 to +125	
MC33063A, SC33063A		-40 to +85	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Maximum package power dissipation limits must be observed.

2. This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL–STD–883, Method 3015. Machine Model Method 400 V.

3. NCV prefix is for automotive and other applications requiring site and change control.



Characteristics	Symbol	Min	Тур	Max	Unit
OSCILLATOR					
Frequency (V <sub>Pin 5</sub> = 0 V, C <sub>T</sub> = 1.0 nF, T <sub>A</sub> = 25°C)	f <sub>osc</sub>	24	33	42	kHz
Charge Current (V <sub>CC</sub> = 5.0 V to 40 V, $T_A = 25^{\circ}C$ )	I <sub>chg</sub>	24	35	42	μΑ
Discharge Current (V_{CC} = 5.0 V to 40 V, T_A = 25 $^{\circ}\text{C}$ )	I <sub>dischg</sub>	140	220	260	μΑ
Discharge to Charge Current Ratio (Pin 7 to $V_{CC}$ , $T_A = 25^{\circ}C$ )	I <sub>dischg</sub> /I <sub>chg</sub>	5.2	6.5	7.5	_
Current Limit Sense Voltage ( $I_{chg} = I_{dischg}, T_A = 25^{\circ}C$ )	V <sub>ipk(sense)</sub>	250	300	350	mV
OUTPUT SWITCH (Note 5)					
Saturation Voltage, Darlington Connection (I <sub>SW</sub> = 1.0 A, Pins 1, 8 connected)	V <sub>CE(sat)</sub>	-	1.0	1.3	V
Saturation Voltage (Note 6) (I <sub>SW</sub> = 1.0 A, R <sub>Pin 8</sub> = 82 $\Omega$ to V <sub>CC</sub> , Forced $\beta \simeq 20$ )	V <sub>CE(sat)</sub>	-	0.45	0.7	V
DC Current Gain (I_SW = 1.0 A, V_CE = 5.0 V, T_A = 25°C)	h <sub>FE</sub>	50	75	-	-
Collector Off–State Current (V <sub>CE</sub> = 40 V)	I <sub>C(off)</sub>	-	0.01	100	μΑ
COMPARATOR					
Threshold Voltage $T_A = 25^{\circ}C$ $T_A = T_{low}$ to $T_{high}$	V <sub>th</sub>	1.225 1.21	1.25 -	1.275 1.29	V
Threshold Voltage Line Regulation (V <sub>CC</sub> = 3.0 V to 40 V) MC33063, MC34063 MC33063V, NCV33063	Reg <sub>line</sub>		1.4 1.4	5.0 6.0	mV
Input Bias Current (V <sub>in</sub> = 0 V)	I <sub>IB</sub>	-	-20	-400	nA
TOTAL DEVICE	•	•			
Supply Current ( $V_{00} = 5.0$ V to $40$ V Cr = 1.0 nF. Pin 7 = $V_{00}$	laa	1		4.0	m۵

Supply Current (V <sub>CC</sub> = 5.0 V to 40 V, C <sub>T</sub> = 1.0 nF, Pin 7 = V <sub>CC</sub> , V <sub>Pin 5</sub> > V <sub>th</sub> , Pin 2 = GND, remaining pins open)	I <sub>CC</sub>	-	-	4.0	mA	
--	-----------------	---	---	-----	----	--

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4.

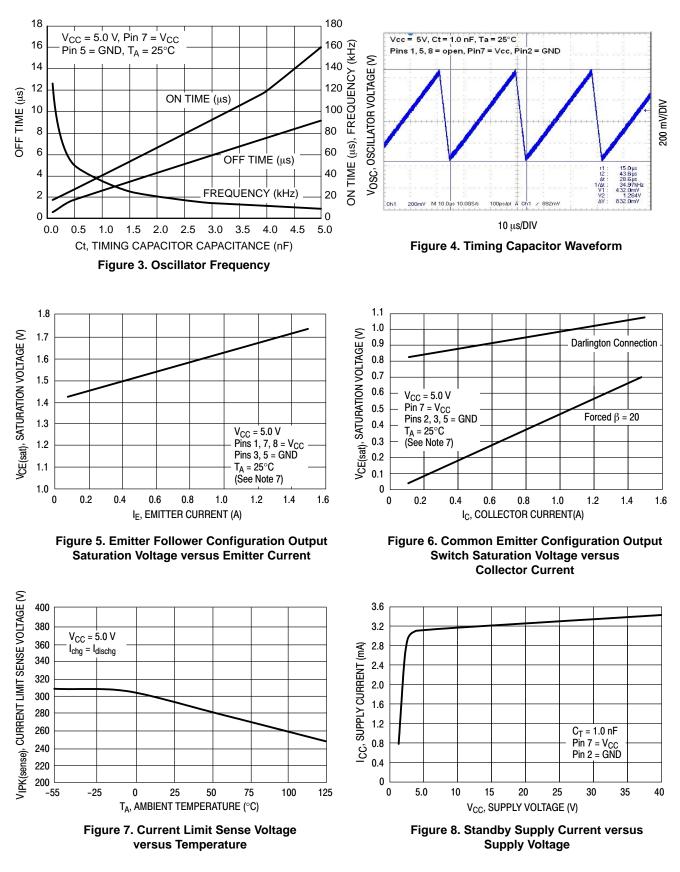
 $T_{low} = 0^{\circ}C \text{ for MC34063}, SC34063; -40^{\circ}C \text{ for MC33063}, SC33063, MC33063V, NCV33063$  $T_{high} = +70^{\circ}C \text{ for MC34063}, SC34063; +85^{\circ}C \text{ for MC33063}, SC33063; +125^{\circ}C \text{ for MC33063V}, NCV33063$ Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.5. 6. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mÅ) and high driver currents

(≥ 30 mÅ), it may take up to 2.0 µs for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

Forced  $\beta$  of output switch :  $\frac{IC \text{ output}}{IC \text{ driver} - 7.0 \text{ mA}^*} \ge 10$ 

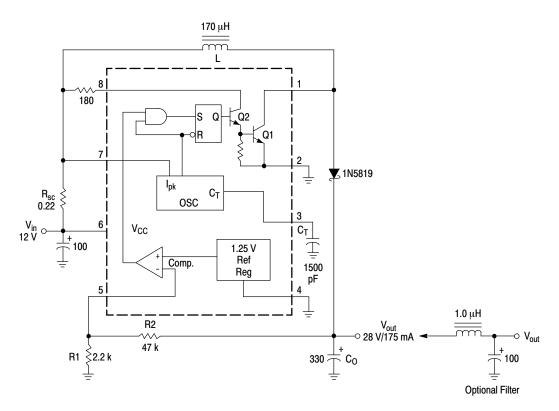
\* The 100 Ω resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.





7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



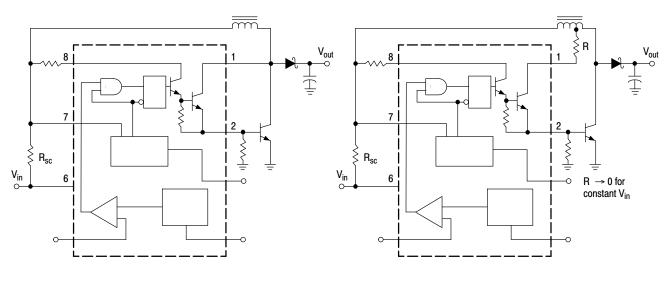


Test	Conditions	Results
Line Regulation	$V_{in}$ = 8.0 V to 16 V, $I_{O}$ = 175 mA	30 mV = ±0.05%
Load Regulation	$V_{in}$ = 12 V, I <sub>O</sub> = 75 mA to 175 mA	10 mV = ±0.017%
Output Ripple	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	400 mVpp
Efficiency	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	87.7%
Output Ripple With Optional Filter	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	40 mVpp

Figure	9.	Step-Up	Converter
--------	----	---------	-----------







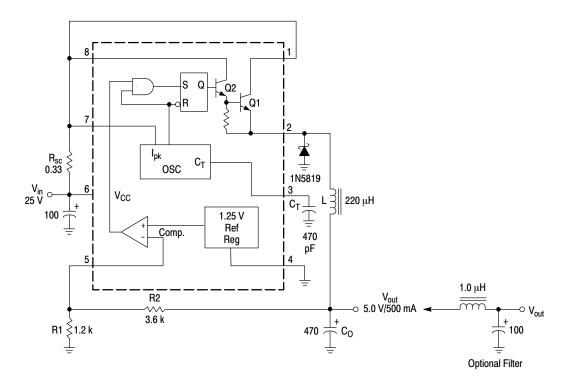


9a. External NPN Switch

9b. External NPN Saturated Switch (See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 µs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.





Test	Conditions	Results
Line Regulation	$V_{in}$ = 15 V to 25 V, I <sub>O</sub> = 500 mA	12 mV = ±0.12%
Load Regulation	$V_{in} = 25 \text{ V}, I_{O} = 50 \text{ mA to } 500 \text{ mA}$	3.0 mV = ±0.03%
Output Ripple	$V_{in} = 25 \text{ V}, I_0 = 500 \text{ mA}$	120 mVpp
Short Circuit Current	$V_{in} = 25 \text{ V}, \text{ R}_{L} = 0.1 \Omega$	1.1 A
Efficiency	$V_{in} = 25 \text{ V}, I_0 = 500 \text{ mA}$	83.7%
Output Ripple With Optional Filter	$V_{in} = 25 \text{ V}, I_0 = 500 \text{ mA}$	40 mVpp

Figure 11. Step–Down Converter

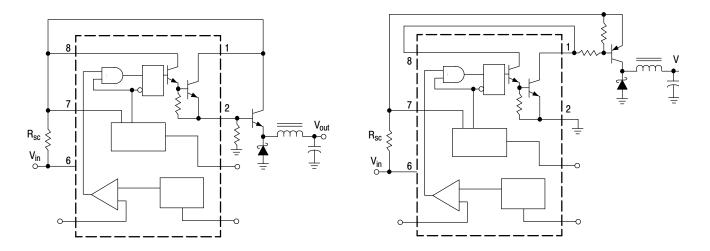
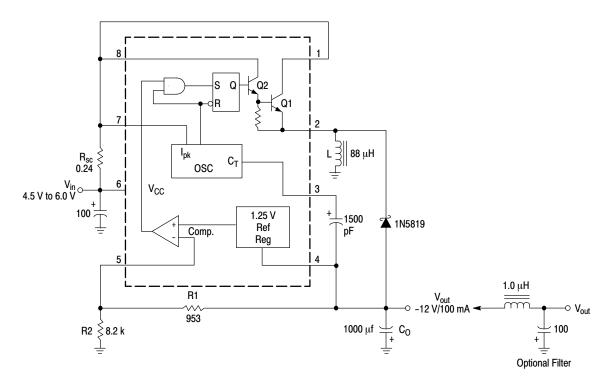


Figure 12. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch





Test	Conditions	Results
Line Regulation	$V_{in}$ = 4.5 V to 6.0 V, I <sub>O</sub> = 100 mA	3.0 mV = ±0.012%
Load Regulation	$V_{in} = 5.0 \text{ V}, I_0 = 10 \text{ mA to } 100 \text{ mA}$	0.022 V = ±0.09%
Output Ripple	$V_{in} = 5.0 \text{ V}, I_0 = 100 \text{ mA}$	500 mVpp
Short Circuit Current	$V_{in}$ = 5.0 V, $R_L$ = 0.1 $\Omega$	910 mA
Efficiency	$V_{in} = 5.0 \text{ V}, I_0 = 100 \text{ mA}$	62.2%
Output Ripple With Optional Filter	V <sub>in</sub> = 5.0 V, I <sub>O</sub> = 100 mA	70 mVpp

Figure 13. Voltage Inverting Converter

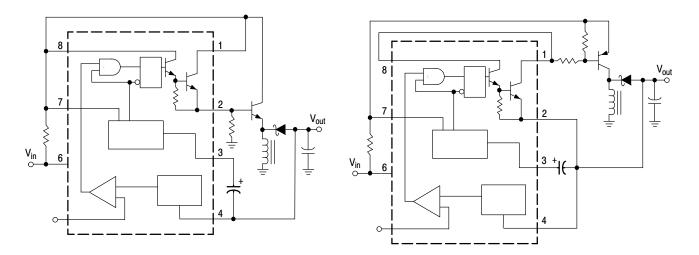
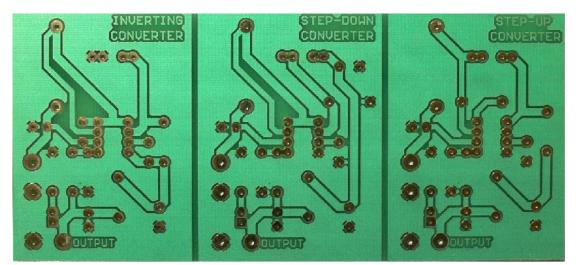
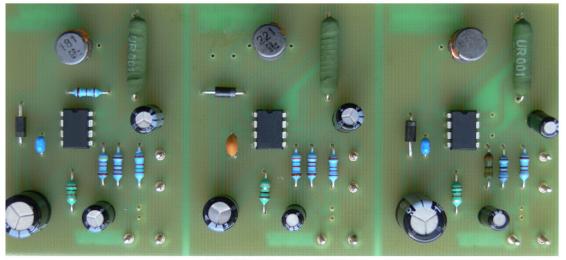


Figure 14. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A 13a. External NPN Switch 13b. External PNP Saturated Switch





(Bottom Side)



(Top View, Component Side)

#### Figure 15. Printed Circuit Board and Component Layout (Circuits of Figures 9, 11, 13)

#### **INDUCTOR DATA**

Converter	Inductance (μH)	Turns/Wire
Step-Up	170	38 Turns of #22 AWG
Step-Down	220	48 Turns of #22 AWG
Voltage-Inverting	88	28 Turns of #22 AWG

All inductors are wound on Magnetics Inc. 55117 toroidal core.



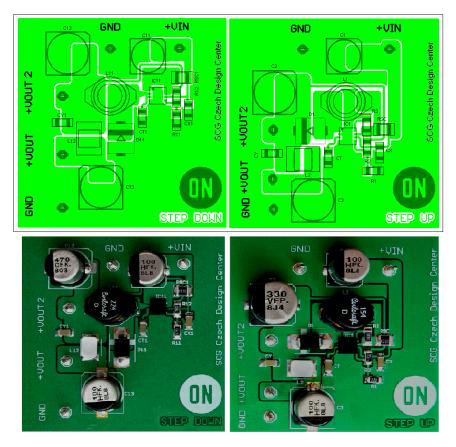


Figure 16. Printed Circuit Board for DFN Device



Calculation	Step-Up	Step-Down	Voltage-Inverting
t <sub>on</sub> /t <sub>off</sub>	$\frac{V_{out} + V_{F} - V_{in(min)}}{V_{in(min)} - V_{sat}}$	Vout + V <sub>F</sub> V <sub>in(min)</sub> - V <sub>sat</sub> - V <sub>out</sub>	lV <sub>out</sub> l + V <sub>F</sub> V <sub>in</sub> − V <sub>sat</sub>
$(t_{on} + t_{off})$	$\frac{1}{f}$	<u>1</u> f	<u>1</u> f
t <sub>off</sub>	$\frac{\frac{t_{on} + t_{off}}{t_{off}}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{t_{off}}}{\frac{t_{on}}{t_{off}} + 1}$
t <sub>on</sub>	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$
CT	4.0 x 10 <sup>-5</sup> t <sub>on</sub>	4.0 x 10 <sup>−5</sup> t <sub>on</sub>	4.0 x 10 <sup>-5</sup> t <sub>on</sub>
I <sub>pk(switch)</sub>	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$	<sup>2I</sup> out(max)	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$
R <sub>sc</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>
L <sub>(min)</sub>	$\left(rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}} ight)^t$ on(max)	$\left(\frac{(V_{in(min)} - V_{sat} - V_{out})}{I_{pk(switch)}}\right) t_{on(max)}$	$\left(rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}} ight)^t$ on(max)
C <sub>O</sub>	9 <mark>l<sub>out</sub>t<sub>on</sub> V<sub>ripple(pp)</sub></mark>	$\frac{I_{pk(switch)}(t_{on} + t_{off})}{^{8V}ripple(pp)}$	9 <mark>l<sub>out</sub>t<sub>on</sub> V<sub>ripple(pp)</sub></mark>

 $V_{sat}$  = Saturation voltage of the output switch.

 $V_F$  = Forward voltage drop of the output rectifier.

#### The following power supply characteristics must be chosen:

V<sub>in</sub> – Nominal input voltage.

 $V_{out}$  - Desired output voltage,  $|V_{out}| = 1.25 \left(1 + \frac{R2}{R1}\right)$ 

 $I_{out}$  – Desired output current.  $f_{min}$  – Minimum desired output switching frequency at the selected values of V<sub>in</sub> and I<sub>O</sub>.

Vripple(pp) – Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

**NOTE:** For further information refer to Application Note AN920A/D and AN954/D.

#### Figure 17. Design Formula Table





#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>	
MC33063ADG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
SC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
MC33063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail	
MC33063AVDG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC33063AVDR2G	SOIC-8 (Pb-Free)		
NCV33063AVDR2G*	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
MC33063AVPG	PDIP-8 (Pb-Free)	50 Units / Rail	
MC34063ADG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC34063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
MC34063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail	

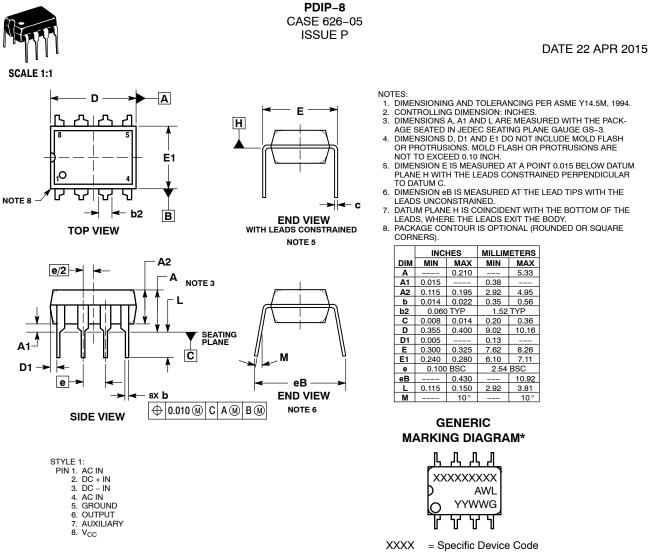
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*NCV33063A: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

SENSEFET is a trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.



# onsemi



A = Assembly Location

- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb–Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42420B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	PDIP-8		PAGE 1 OF 1		
the right to make changes without furth purpose, nor does <b>onsemi</b> assume an	onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights of others.				

© Semiconductor Components Industries, LLC, 2019

# onsemi



\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2		
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.					

#### SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

#### STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

SOURCE 1/DRAIN 2

7.

8. GATE 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights or others.

7.

8

COLLECTOR, #1

COLLECTOR, #1

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>